

isc Silicon NPN Power Transistor

3DD325

DESCRIPTION

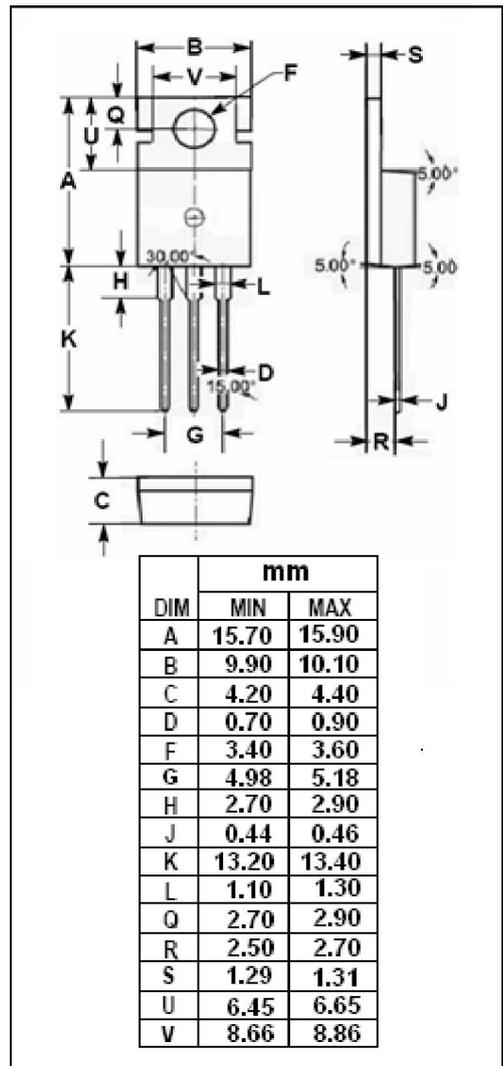
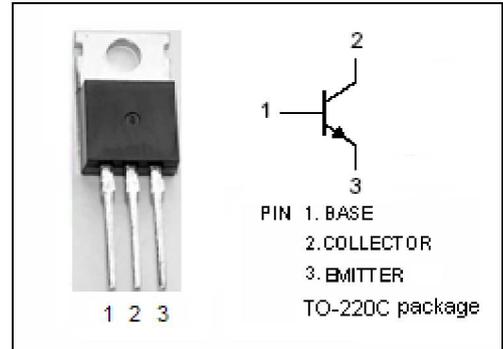
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 50V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.5V(\text{Max}) @ I_C = 0.5A$

APPLICATIONS

- Designed for B/W TV vertical output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	3DD325A	30
		3DD325B	50
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.8	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**3DD325****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; I_B=0$	3DD325A	30		V
			3DD325B	50		
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=0.5\text{mA}; I_C=0$	4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.5\text{A}; I_B=50\text{mA}$			0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=50\text{V}; I_E=0$			10	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=15\text{V}; I_B=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			0.1	mA
h_{FE}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=3\text{V}$	50		200	

◆ **h_{FE} Classifications**

Green	Blue	Purple	Grey
50-70	70-100	100-140	140-200